

OPA9421

Infrared LED Chip

GaAs /GaAs

1. Material Substrate GaAs (N Type)
 Epitaxial Layer GaAs (P/N Type)

2. Electrode N (Cathode) Side Gold Alloy
 P (Anode) Side Gold Alloy

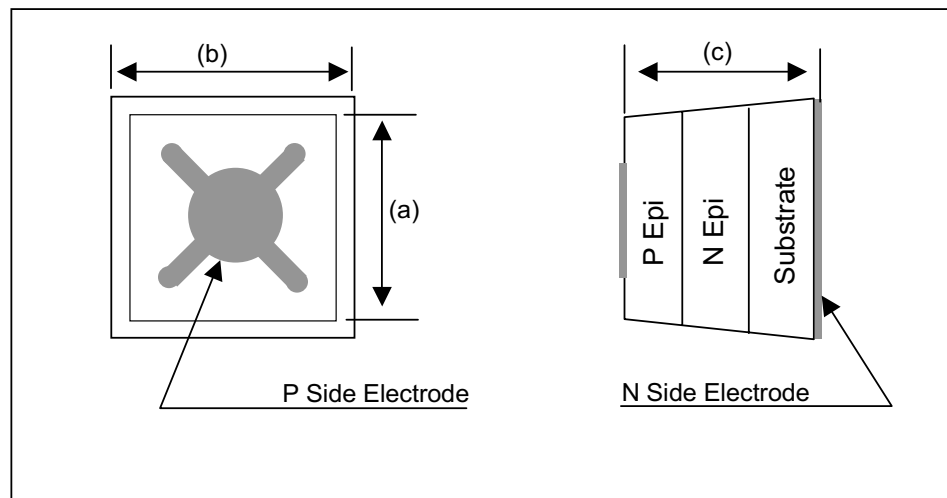
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.2		V	$I_F=20\text{mA}$
	$V_{F(2)}$		1.4	1.6	V	$I_F=100\text{mA}$
Reverse Voltage	V_R	5.0	30		V	$I_R=10\mu\text{A}$
Power	$P_{O(1)}$		4		mW	$I_F=20\text{mA}$
	$P_{O(2)}$	8	12		mW	$I_F=100\text{mA}$
Wavelength	λ_P		940		nm	$I_F=20\text{mA}$
	$\Delta\lambda$		45		nm	$I_F=20\text{mA}$

Note : Assembled into T1³/₄ plastic package.

4. Mechanical Data

- (a) Emission Area ----- 12mil × 12mil
- (b) Bottom Area ----- 14mil × 14mil
- (c) Chip Thickness ----- 11mil



Knowledge*on Inc.

For more information, visit our website at www.knowledge-on.com

513-37 Eoyang-dong, Iksan, 570-210, Korea. Tel: +82-63-839-1111. Fax: +82-63-835-8259

